

BR2SD2150Q

Rev.A Aug.-2022

/ Descriptions

SOT-89 NPN Silicon NPN transistor in a SOT-89 Plastic Package.

/ Features

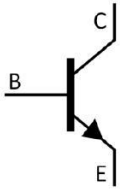
BR2SB1424Q AEC-Q101

Low $V_{CE(sat)}$, excellent current gain characteristic, Complementary to BR2SB1424Q, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

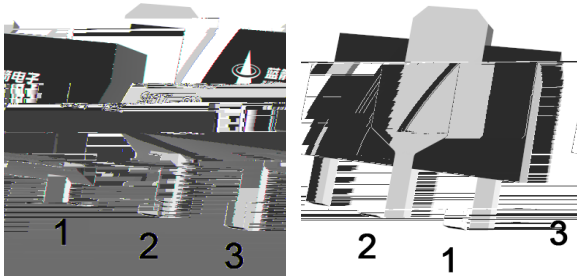
/ Applications

General purpose amplifier, Meet the stringent requirements of automotive applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

/ h_{FE} Classifications & Marking

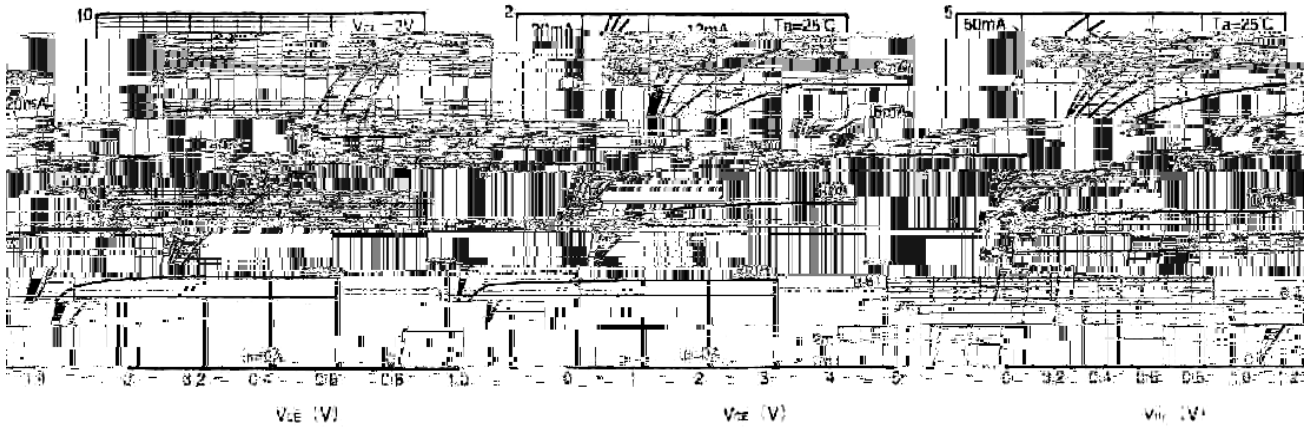
h_{FE} Classifications Symbol	Q	R	S	E
h_{FE} Range	120 270	180 390	270 560	390 820
Marking	QCFQ**	QCFR**	QCFS**	QCFE**

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current-Continuous	$I_{C(DC)}$	3.0	A
Collector Base-Continuous(Pulse)*	$I_{C(Pulse)^*}$	5.0	A
Collector Power Dissipation	P_C	500	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

*:Single pulse $P_w=10ms$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=50\mu A$	40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0mA$	20			V
Emitter to Base Breakdown Voltage	V_{EBO}	I				

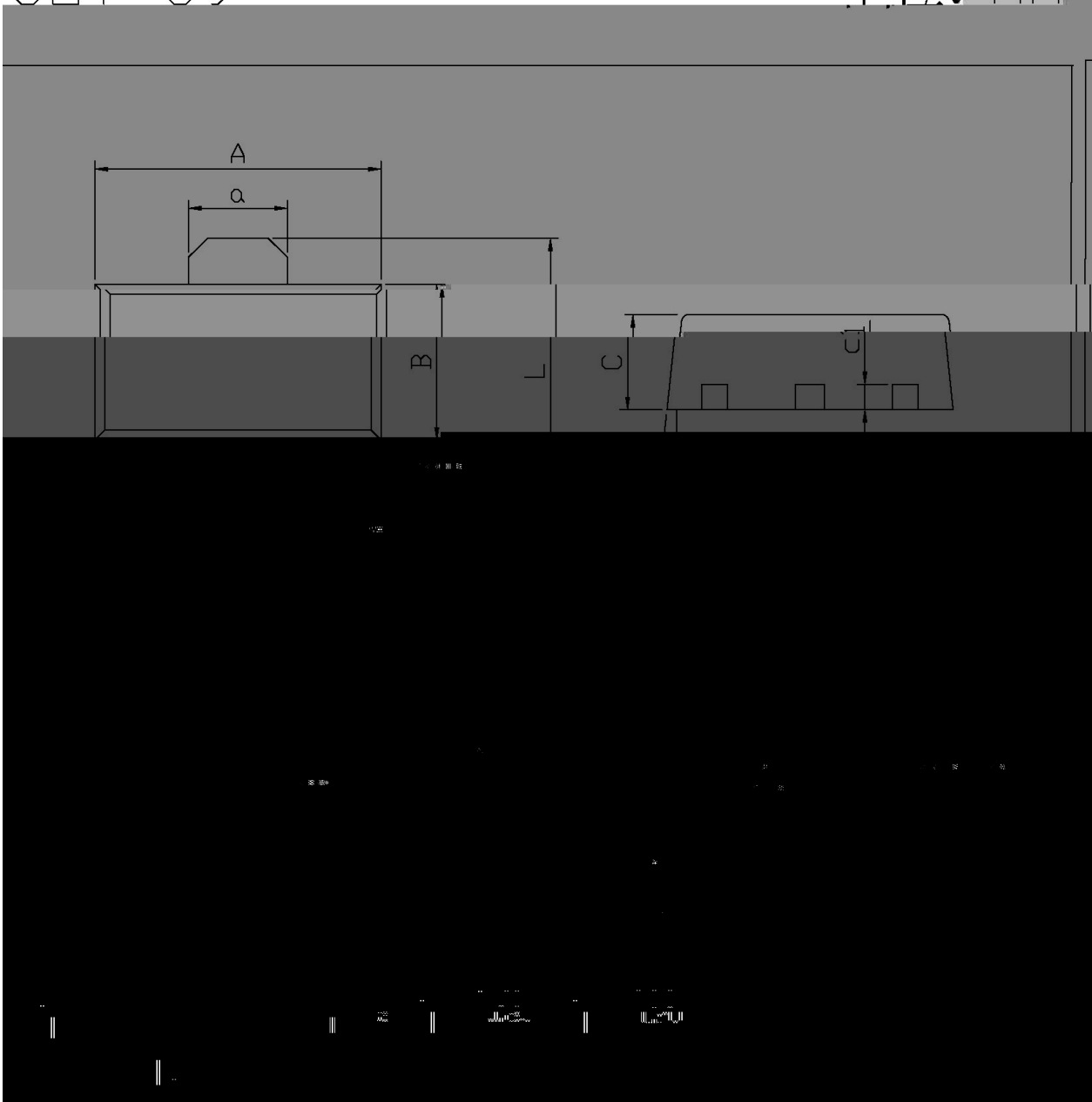
/ Electrical Characteristic Curve



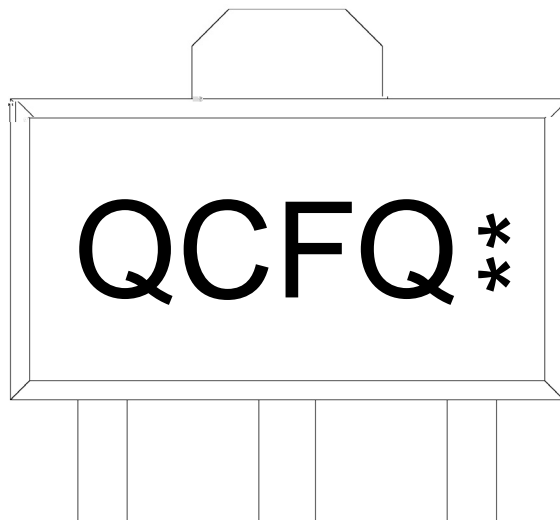
/ Package Dimensions

SOT-89

单位: mm



/ Marking Instructions



Q

CF

Q: h_{FE}

**

Note:

Q: Automobile halogen-free product Code

CF: Product Type

Q h_{FE} Classifications Symbol

** : Lot No. Code, code change with Lot No

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DATA SHEET